# MPSA42, MPSA43

**MPSA42 is a Preferred Device**

# High Voltage Transistors

## NPN Silicon

ON Semiconductor™

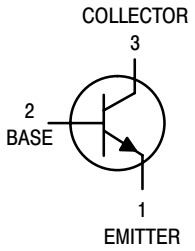
**http://onsemi.com**

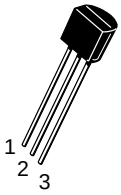
### MAXIMUM RATINGS

| Rating | Symbol | Value | Unit |
|---|---|---|---|
| Collector–Emitter Voltage<br>MPSA43<br>MPSA42 | $V_{CEO}$ | <br>200<br>300 | Vdc |
| Collector–Base Voltage<br>MPSA43<br>MPSA42 | $V_{CBO}$ | <br>200<br>300 | Vdc |
| Emitter–Base Voltage | $V_{EBO}$ | 6.0 | Vdc |
| Collector Current – Continuous | $I_C$ | 500 | mAdc |
| Total Device Dissipation<br>@ $T_A$ = 25°C<br>Derate above 25°C | $P_D$ | <br>625<br>5.0 | <br>mW<br>mW/°C |
| Total Device Dissipation<br>@ $T_C$ = 25°C<br>Derate above 25°C | $P_D$ | <br>1.5<br>12 | <br>Watts<br>mW/°C |
| Operating and Storage Junction Temperature Range | $T_J$, $T_{stg}$ | –55 to +150 | °C |

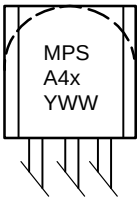
### THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|---|---|---|---|
| Thermal Resistance, Junction to Ambient | $R_{\theta JA}$ | 200 | °C/mW |
| Thermal Resistance, Junction to Case | $R_{\theta JC}$ | 83.3 | °C/mW |




### MARKING DIAGRAM




MPSA4x = Specific Device Code
x = 2 or 3
Y = Year
W = Work Week

### ORDERING INFORMATION

| Device | Package | Shipping |
|---|---|---|
| MPSA42 | TO–92 | 5000 Units/Box |
| MPSA42RLRA | TO–92 | 2000/Tape & Reel |
| MPSA42RLRE | TO–92 | 2000/Tape & Reel |
| MPSA42RLRF | TO–92 | 5000 Units/Box |
| MPSA42RLRM | TO–92 | 2000/Ammo Pack |
| MPSA42RLRP | TO–92 | 2000/Ammo Pack |
| MPSA43 | TO–92 | 5000 Units/Box |
| MPSA43RLRA | TO–92 | 2000/Tape & Reel |

**Preferred** devices are recommended choices for future use and best overall value.

**ELECTRICAL CHARACTERISTICS** ($T_A$ = 25°C unless otherwise noted)

| Characteristic | | Symbol | Min | Max | Unit |
|---|---|---|---|---|---|
| **OFF CHARACTERISTICS** | | | | | |
| Collector–Emitter Breakdown Voltage (Note 1.) | | $V_{(BR)CEO}$ | | | Vdc |
| ($I_C$ = 1.0 mAdc, $I_B$ = 0) | MPSA42 | | 300 | – | |
| | MPSA43 | | 200 | – | |
| Collector–Base Breakdown Voltage | | $V_{(BR)CBO}$ | | | Vdc |
| ($I_C$ = 100 μAdc, $I_E$ = 0) | MPSA42 | | 300 | – | |
| | MPSA43 | | 200 | – | |
| Emitter–Base Breakdown Voltage | | $V_{(BR)EBO}$ | 6.0 | – | Vdc |
| ($I_E$ = 100 μAdc, $I_C$ = 0) | | | | | |
| Collector Cutoff Current | | $I_{CBO}$ | | | μAdc |
| ($V_{CB}$ = 200 Vdc, $I_E$ = 0) | MPSA42 | | – | 0.1 | |
| ($V_{CB}$ = 160 Vdc, $I_E$ = 0) | MPSA43 | | – | 0.1 | |
| Emitter Cutoff Current | | $I_{EBO}$ | | | μAdc |
| ($V_{EB}$ = 6.0 Vdc, $I_C$ = 0) | MPSA42 | | – | 0.1 | |
| ($V_{EB}$ = 4.0 Vdc, $I_C$ = 0) | MPSA43 | | – | 0.1 | |
| **ON CHARACTERISTICS** (Note 1.) | | | | | |
| DC Current Gain | | $h_{FE}$ | | | – |
| ($I_C$ = 1.0 mAdc, $V_{CE}$ = 10 Vdc) | | | 25 | – | |
| ($I_C$ = 10 mAdc, $V_{CE}$ = 10 Vdc) | | | 40 | – | |
| ($I_C$ = 30 mAdc, $V_{CE}$ = 10 Vdc) | | | 40 | – | |
| Collector–Emitter Saturation Voltage | | $V_{CE(sat)}$ | | | Vdc |
| ($I_C$ = 20 mAdc, $I_B$ = 2.0 mAdc) | MPSA42 | | – | 0.5 | |
| | MPSA43 | | – | 0.4 | |
| Base–Emitter Saturation Voltage | | $V_{BE(sat)}$ | – | 0.9 | Vdc |
| ($I_C$ = 20 mAdc, $I_B$ = 2.0 mAdc) | | | | | |
| **SMALL–SIGNAL CHARACTERISTICS** | | | | | |
| Current–Gain – Bandwidth Product | | $f_T$ | 50 | – | MHz |
| ($I_C$ = 10 mAdc, $V_{CE}$ = 20 Vdc, f = 100 MHz) | | | | | |
| Collector–Base Capacitance | | $C_{cb}$ | | | pF |
| ($V_{CB}$ = 20 Vdc, $I_E$ = 0, f = 1.0 MHz) | MPSA42 | | – | 3.0 | |
| | MPSA43 | | – | 4.0 | |

1. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

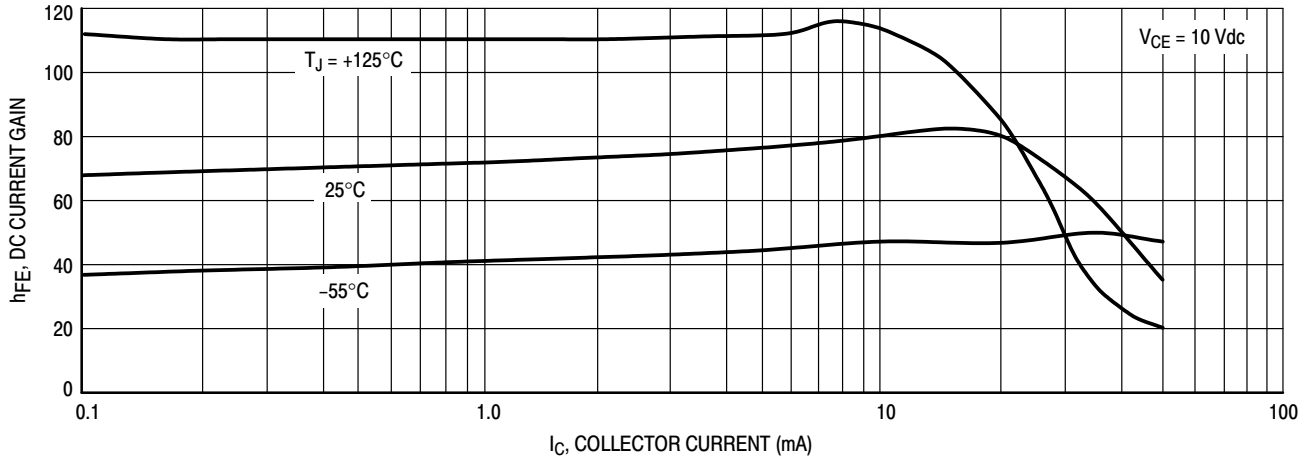



**Figure 1. DC Current Gain**

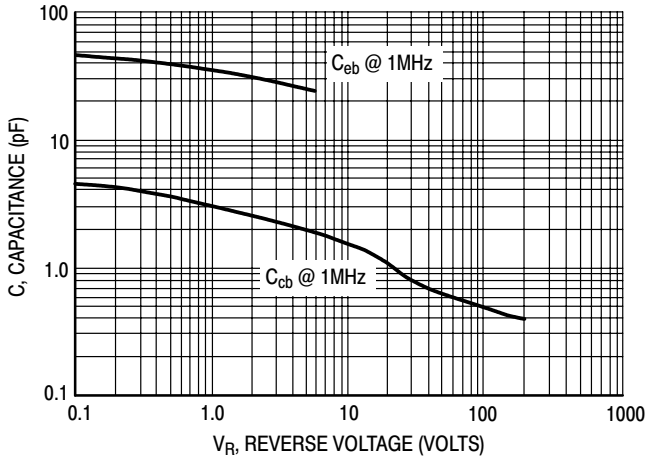



**Figure 2. Capacitance**

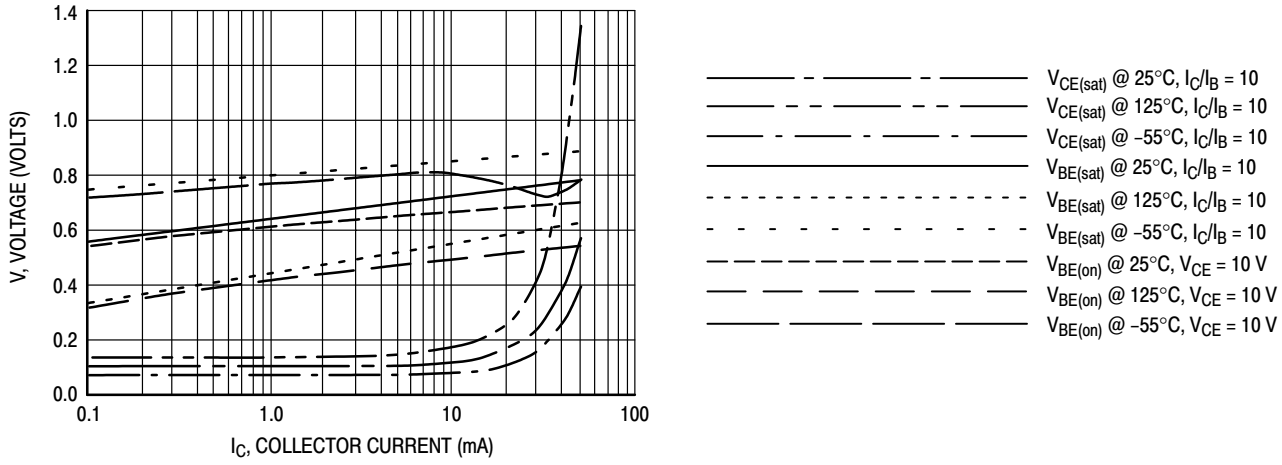
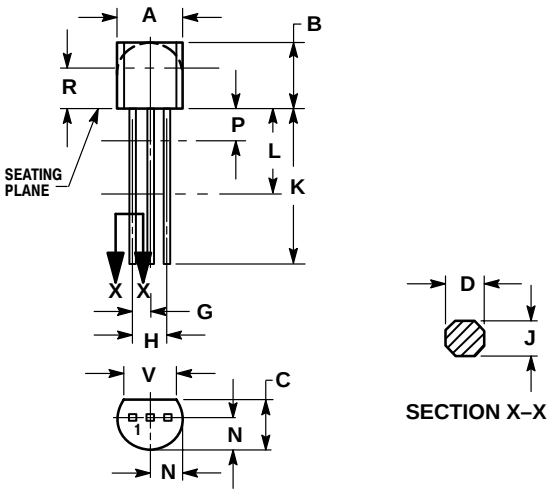



**Figure 3. “ON” Voltages**

## PACKAGE DIMENSIONS

**TO–92**
**TO–226AA**
CASE 29–11
ISSUE AL




NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

| | INCHES | | MILLIMETERS | |
|---|---|---|---|---|
| DIM | MIN | MAX | MIN | MAX |
| A | 0.175 | 0.205 | 4.45 | 5.20 |
| B | 0.170 | 0.210 | 4.32 | 5.33 |
| C | 0.125 | 0.165 | 3.18 | 4.19 |
| D | 0.016 | 0.021 | 0.407 | 0.533 |
| G | 0.045 | 0.055 | 1.15 | 1.39 |
| H | 0.095 | 0.105 | 2.42 | 2.66 |
| J | 0.015 | 0.020 | 0.39 | 0.50 |
| K | 0.500 | --- | 12.70 | --- |
| L | 0.250 | --- | 6.35 | --- |
| N | 0.080 | 0.105 | 2.04 | 2.66 |
| P | --- | 0.100 | --- | 2.54 |
| R | 0.115 | --- | 2.93 | --- |
| V | 0.135 | --- | 3.43 | --- |

STYLE 1:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 14:
PIN 1. EMITTER
2. COLLECTOR
3. BASE



## PUBLICATION ORDERING INFORMATION

**Literature Fulfillment**:
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